


## N-Channel Enhancement Mode Power MOSFET

### Description

The PTI  FESÁ uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

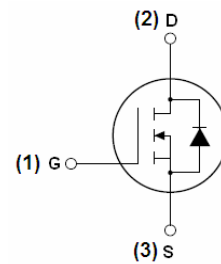
- $V_{DS} = 100V, I_D = 40A$   
 $R_{DS(ON)} < 17m\Omega @ V_{GS}=10V$  (Typ:14m $\Omega$ )
- Special process technology for high ESD capability
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

### Application

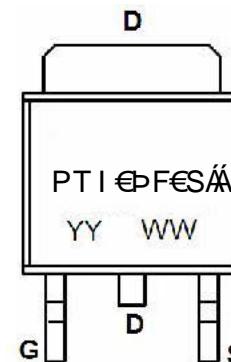
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

**100% UIS TESTED!**

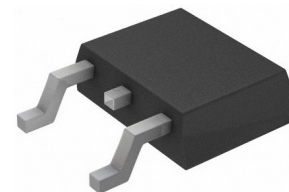
**100%  $\Delta V_{ds}$  TESTED!**



Schematic diagram





Marking and pin assignment



TO-252-2L top view

## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
PTI  FESÁ	PTI  FESÁ	TO-252-2L	-	-	-

## Absolute Maximum Ratings ( $T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	40	A
Drain Current-Continuous( $T_C=100^{\circ}C$ )	$I_D(100^{\circ}C)$	28	A
Pulsed Drain Current	$I_{DM}$	160	A
Maximum Power Dissipation	$P_D$	140	W
Derating factor	-	0.94	W/ $^{\circ}C$
Single pulse avalanche energy (Note 5)	$E_{AS}$	520	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^{\circ}C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case(Note 2)	$R_{\theta JC}$	1.07	$^{\circ}C/W$
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### Electrical Characteristics ( $T_C=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100	110	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=28A$	-	14	17	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=25V, I_D=28A$	32	-	-	S
<b>Dynamic Characteristics (Note 4)</b>						
Input Capacitance	$C_{ISS}$	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0MHz$	-	3400	-	PF
Output Capacitance	$C_{OSS}$		-	290	-	PF
Reverse Transfer Capacitance	$C_{RSS}$		-	221	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=2A, R_L=15\Omega,$ $R_G=2.5\Omega, V_{GS}=10V$	-	15	-	nS
Turn-on Rise Time	$t_r$		-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	52	-	nS
Turn-Off Fall Time	$t_f$		-	13	-	nS
Total Gate Charge	$Q_g$	$I_D=30A, V_{DD}=30V, V_{GS}=10V$	-	94	-	nC
Gate-Source Charge	$Q_{gs}$		-	16	-	nC
Gate-Drain Charge	$Q_{gd}$		-	24	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=28A$	-	0.85	1.2	V
Diode Forward Current (Note 2)	$I_S$		-	-	40	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = 28A$	-	33		nS
Reverse Recovery Charge	$Q_{rr}$	$di/dt = 100A/\mu s$ (Note3)	-	54		nC
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^{\circ}C, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

**Test Circuit**

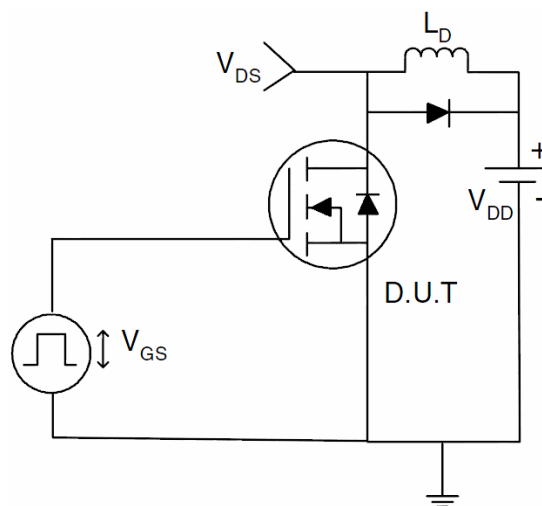
**1)  $E_{AS}$  test Circuit**



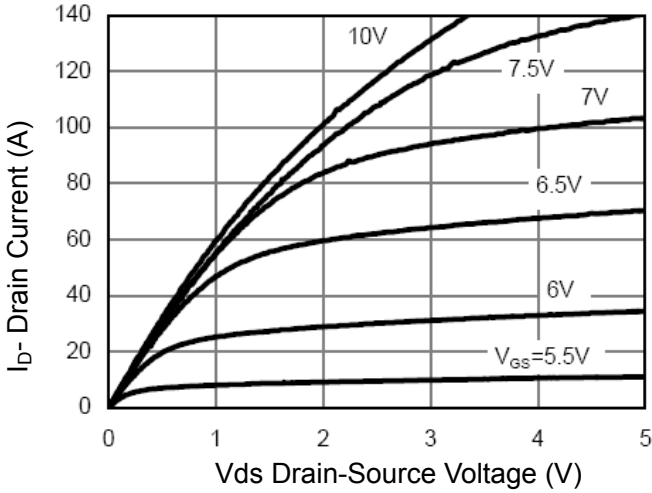
**2) Gate charge test Circuit**



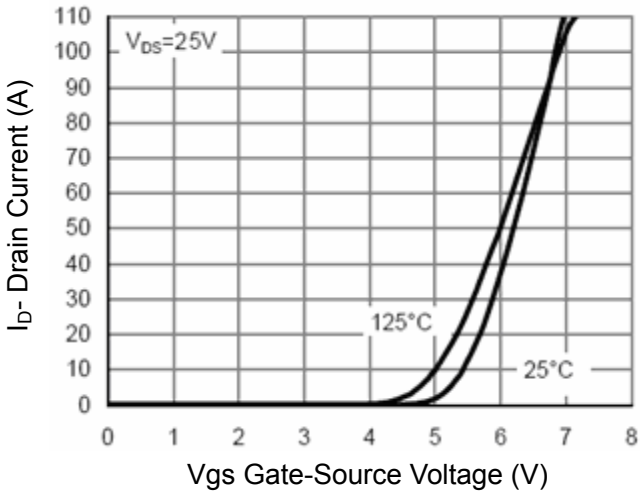
**3) Switch Time Test Circuit**



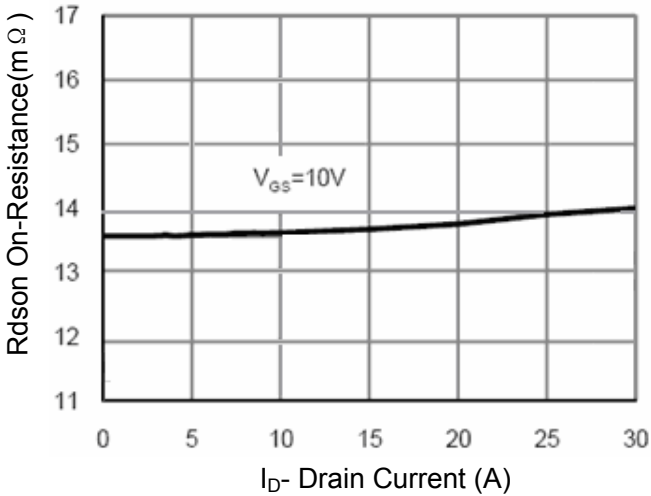
**Typical Electrical and Thermal Characteristics (Curves)**



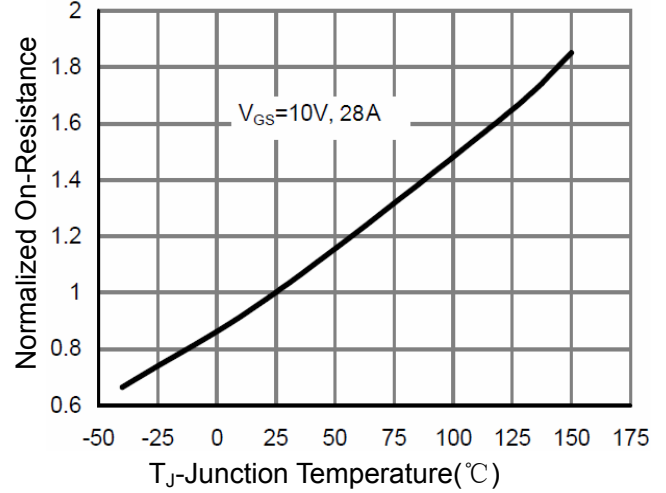
**Figure 1 Output Characteristics**



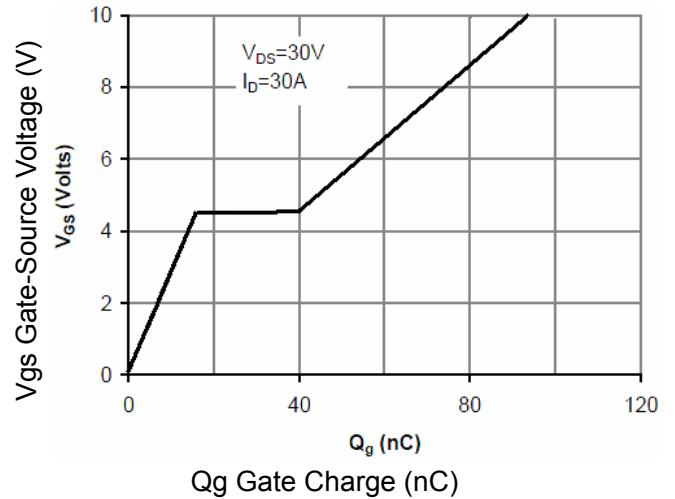
**Figure 2 Transfer Characteristics**



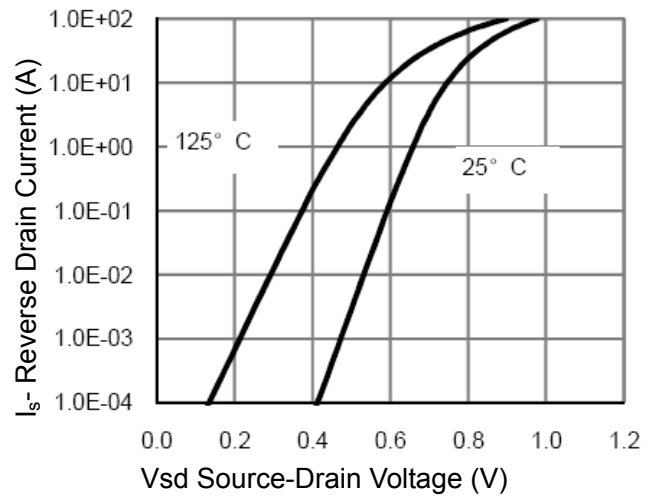
**Figure 3 Rdson- Drain Current**



**Figure 4 Rdson-Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**

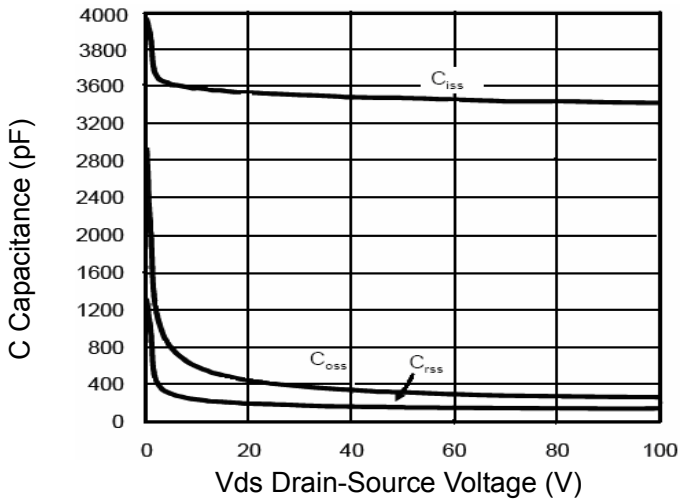


Figure 7 Capacitance vs Vds

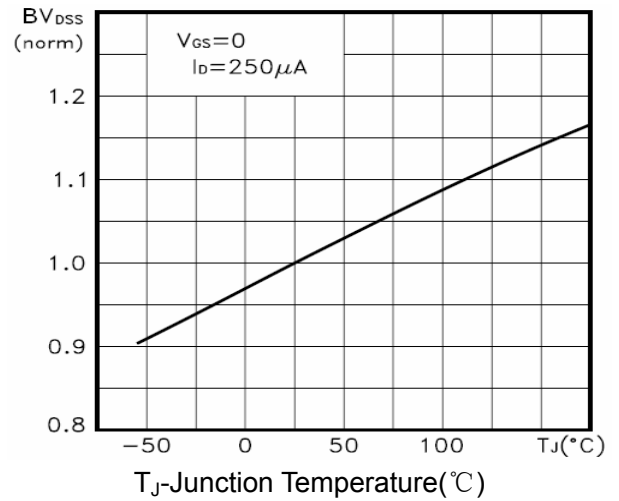


Figure 9  $BV_{DSS}$  vs Junction Temperature

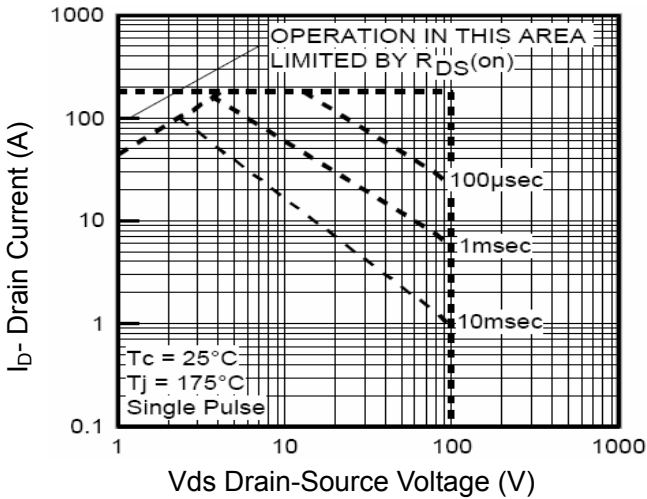


Figure 8 Safe Operation Area

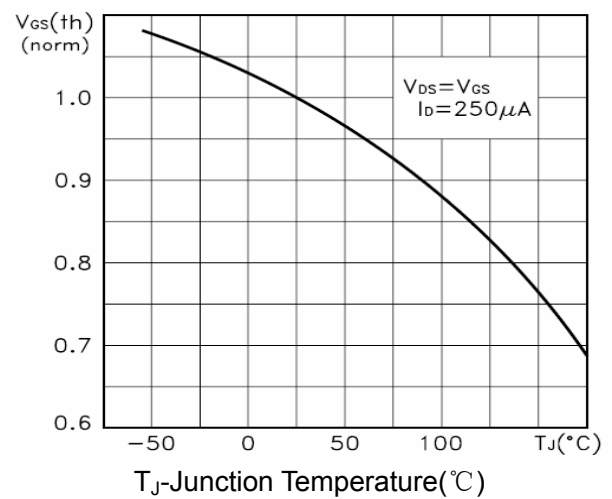


Figure 10  $V_{GS(th)}$  vs Junction Temperature

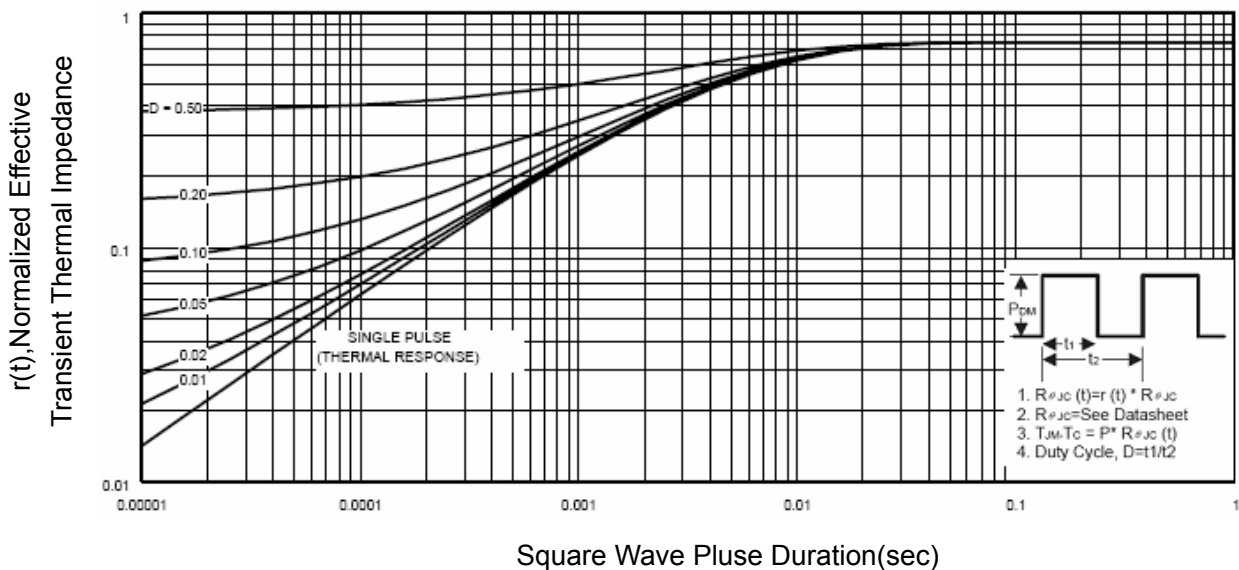
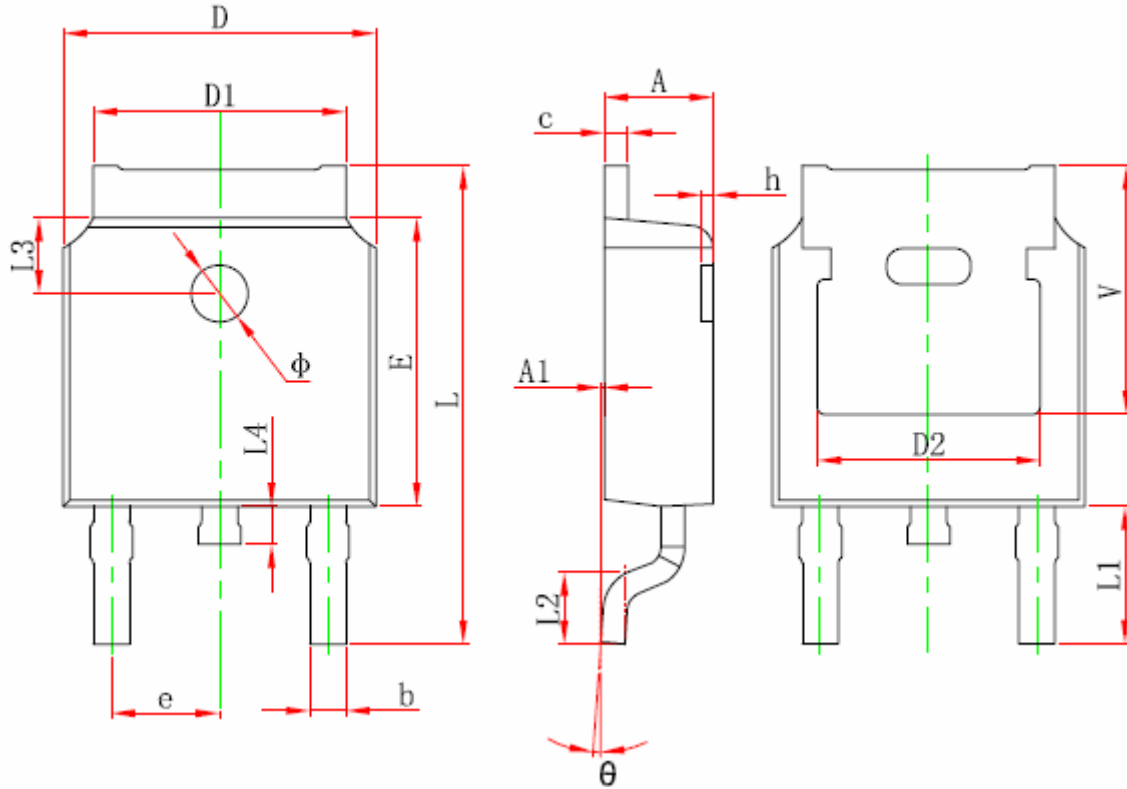


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 REF.		0.190 REF.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 REF.		0.114 REF.	
L2	1.400	1.700	0.055	0.067
L3	1.600 REF.		0.063 REF.	
L4	0.600	1.000	0.024	0.039
φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 REF.		0.211 REF.	

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